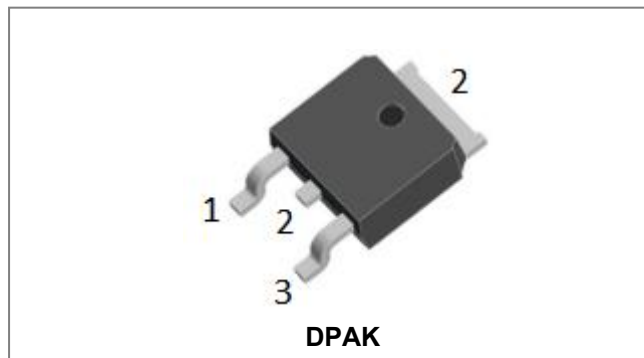


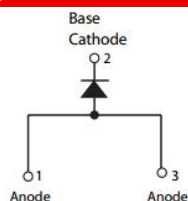
MBRD835 SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Disk drives
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	35	V
Average Rectified Forward Current	I _{F(AV)}	50% duty cycle @T _c =105°C, rectangular wave form	8	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	75	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 8A, Pulse, T _J = 25 °C	0.50	0.51	V
Reverse Current *	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.03	1.4	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	15	35	mA
Junction Capacitance	C _T	@V _R = 5.0V, T _C = 25 °C f _{SIG} = 1MHz	650	740	pF
Typical Series Inductance	L _S	Measured lead to lead 5 mm from package body	5.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	-	6	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

Ratings and Characteristics Curves

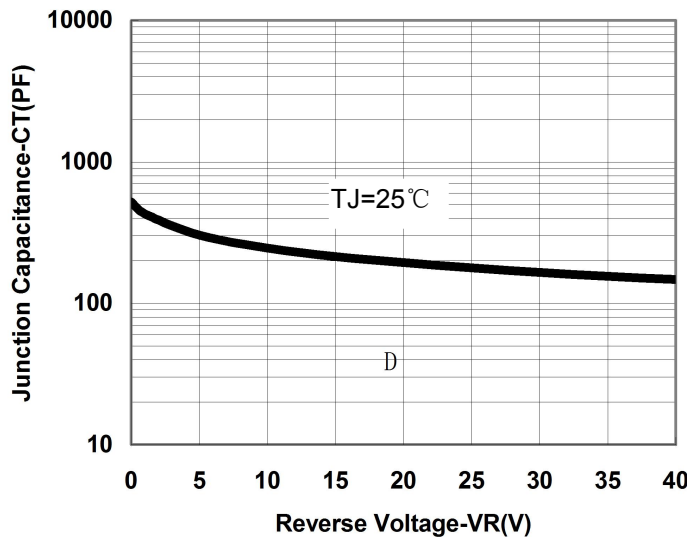


Fig.1-Typical Junction Capacitance

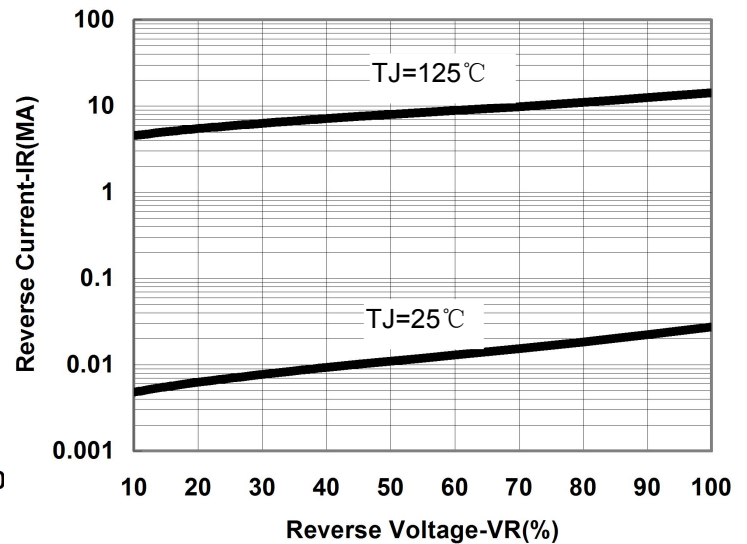


Fig.2-Typical Reverse Characteristics

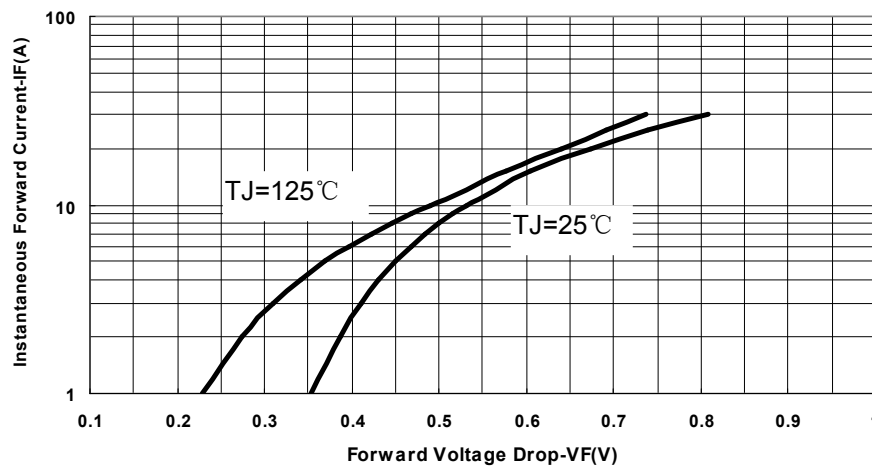
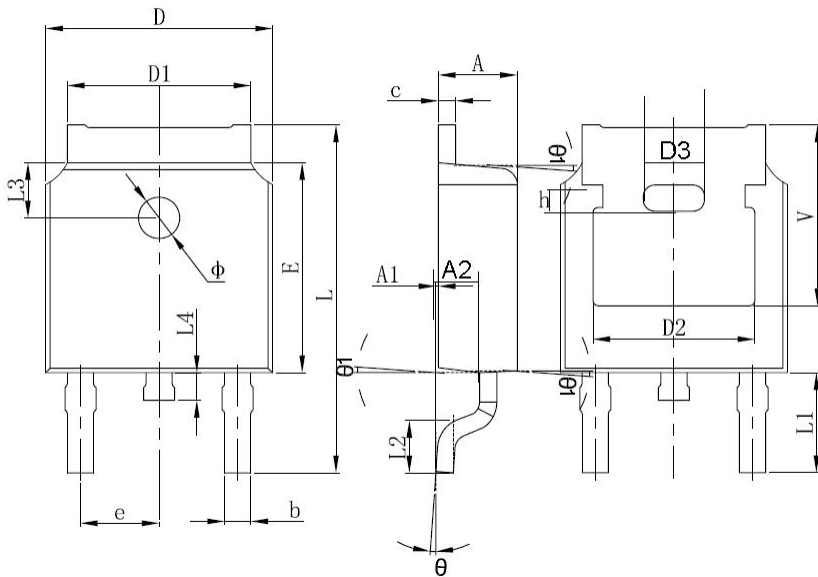


Fig.3-Typical Instantaneous Forward Voltage Characteristics

Mechanical Dimensions DPAK


SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.40	0.087	0.094
A1	0.00	0.127	0.000	0.005
b	0.66	0.86	0.026	0.034
c	0.46	0.60	0.018	0.024
D	6.50	6.70	0.256	0.264
D1	5.13	5.46	0.202	0.215
D2	4.83 REF.		0.190 REF.	
E	6.00	6.20	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.70	10.40	0.381	0.409
L1	2.90 REF.		0.144 REF.	
L2	1.40	1.70	0.055	0.067
L3	1.60 REF.		0.063 REF.	
L4	0.60	1.00	0.024	0.039
Φ	1.10	1.30	0.043	0.051
θ	0°	8°	0°	8°
V	5.35 REF.		0.211 REF.	

Ordering Information

Device	Package	Shipping
MBRD835	DPAK (Pb-Free)	2500pcs / reel

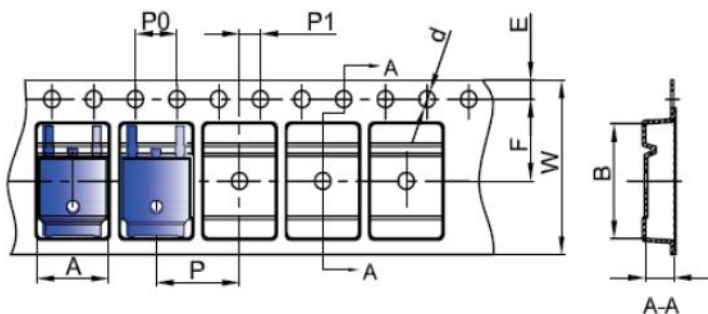
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram


Where XXXXX is YYWWL

MBRD835 = Part Name
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape & Reel Specification DPAK


SYMBOL	Millimeters	
	Min.	Max.
A	6.80	7.00
B	10.40	10.60
C	2.60	2.80
d	Φ1.45	Φ1.65
E	1.65	1.85
F	7.40	7.60
P0	3.90	4.10
P	7.90	8.10
P1	1.90	2.10
W	15.90	16.30

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